

N-channel 800 V, 2.1  $\Omega$  typ., 3 A MDmesh™ K5 Power MOSFETs  
in DPAK, TO-220FP, TO-220 and IPAK packages

Datasheet - production data

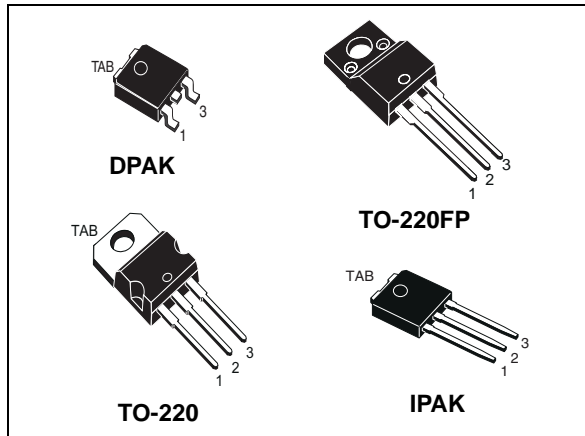
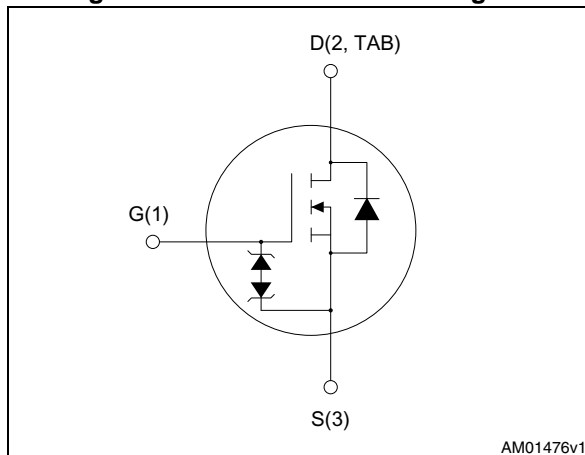


Figure 1. Internal schematic diagram



## Features

Order code	$V_{DS}$	$R_{DS(on)}$ max.	$I_D$	$P_{TOT}$
STD4N80K5	800 V	2.5 $\Omega$	3 A	60 W
STF4N80K5				20 W
STP4N80K5				60 W
STU4N80K5				

- Industry's lowest  $R_{DS(on)}$  x area
- Industry's best figure of merit (FoM)
- Ultra low gate charge
- 100% avalanche tested
- Zener-protected

## Applications

- Switching applications

## Description

These very high voltage N-channel Power MOSFETs are designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1. Device summary

Order code	Marking	Packages	Packaging
STD4N80K5	4N80K5	DPAK	Tape and reel
STF4N80K5		TO-220FP	Tube
STP4N80K5		TO-220	
STU4N80K5		IPAK	

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value			Unit
		DPAK, IPAK	TO-220FP	TO-220	
$V_{DS}$	Drain-source voltage	800			V
$V_{GS}$	Gate- source voltage	±30			V
$I_D$	Drain current (continuous) at $T_C = 25\text{ °C}$	3	3 <sup>(1)</sup>	3	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ °C}$	1.7	1.7 <sup>(1)</sup>	1.7	A
$I_{DM}^{(2)}$	Drain current (pulsed)	12	12 <sup>(1)</sup>	12	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	60	20	60	W
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_J$ max)	1			A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ °C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	74.5			mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	4.5			V/ns
$dv/dt^{(4)}$	MOSFET $dv/dt$ ruggedness	50			V/ns
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t = 1\text{ s}$ , $T_C = 25\text{ °C}$ )		2500		V
$T_J$	Operating junction temperature	-55 to 150			°C
$T_{stg}$	Storage temperature				°C

1. Limited by maximum junction temperature
2. Pulse width limited by safe operating area
3.  $I_{SD} < 3\text{ A}$ ,  $di/dt < 100\text{ A}/\mu\text{s}$ ,  $V_{DS(peak)} \leq V_{(BR)DSS}$
4.  $V_{DS} \leq 640\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value			Unit
		DPAK, IPAK	TO-220FP	TO-220	
$R_{thj-case}$	Thermal resistance junction-case max	2.08	6.25	2.08	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max		62.5		°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	50			°C/W

1. When mounted on 1inch<sup>2</sup> FR-4 board, 2 oz Cu

## 2 Electrical characteristics

(T<sub>case</sub> =25 °C unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0	800			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = 800 V			1	μA
		V <sub>DS</sub> = 800 V, T <sub>C</sub> =125 °C			50	μA
I <sub>GSS</sub>	Gate-body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			±10	μA
V <sub>GS(th)</sub>	Gate threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 100 μA	3	4	5	V
R <sub>DS(on)</sub>	Static drain-source on-resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.5 A		2.1	2.5	Ω

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> = 100 V, f = 1 MHz, V <sub>GS</sub> = 0	-	175	-	pF
C <sub>oss</sub>	Output capacitance		-	18	-	pF
C <sub>rss</sub>	Reverse transfer capacitance		-	0.5	-	pF
C <sub>o(tr)</sub> <sup>(1)</sup>	Equivalent capacitance time related	V <sub>DS</sub> = 0 to 640 V, V <sub>GS</sub> = 0	-	26	-	pF
C <sub>o(er)</sub> <sup>(2)</sup>	Equivalent capacitance energy related	V <sub>DS</sub> = 0 to 640 V, V <sub>GS</sub> = 0	-	11	-	pF
R <sub>g</sub>	Gate input resistance	f=1 MHz, I <sub>D</sub> = 0	-	15	-	Ω
Q <sub>g</sub>	Total gate charge	V <sub>DD</sub> = 640 V, I <sub>D</sub> = 3 A, V <sub>GS</sub> = 10 V (see Figure 19)	-	10.5	-	nC
Q <sub>gs</sub>	Gate-source charge		-	2	-	nC
Q <sub>gd</sub>	Gate-drain charge		-	7.5	-	nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$ , $I_D = 1.5\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 18)	-	16.5	-	ns
$t_r$	Rise time		-	15	-	ns
$t_{d(off)}$	Turn-off-delay time		-	36	-	ns
$t_f$	Fall time		-	21	-	ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		3	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				12	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 3\text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 3\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 20)	-	242		ns
$Q_{rr}$	Reverse recovery charge		-	1.42		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	12		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 3\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$ (see Figure 20)	-	373		ns
$Q_{rr}$	Reverse recovery charge		-	1.98		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	10.5		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 8. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0$	30		-	V

The built-in back-to-back Zener diodes have been specifically designed to enhance the ESD capability of the device. The Zener voltage is appropriate for efficient and cost-effective intervention to protect the device integrity. These integrated Zener diodes thus eliminate the need for external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for DPAK and IPAK

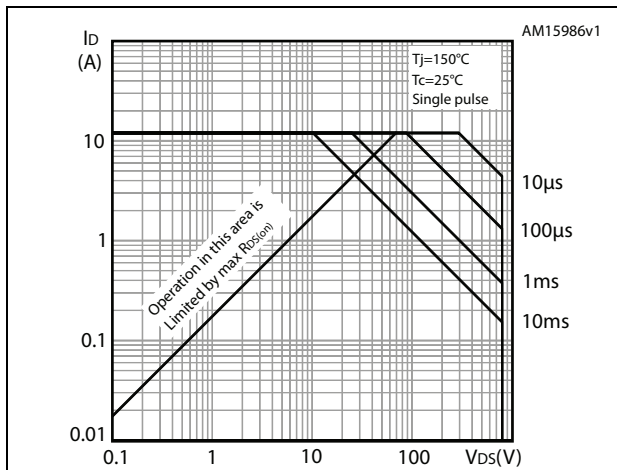


Figure 3. Thermal impedance for DPAK and IPAK

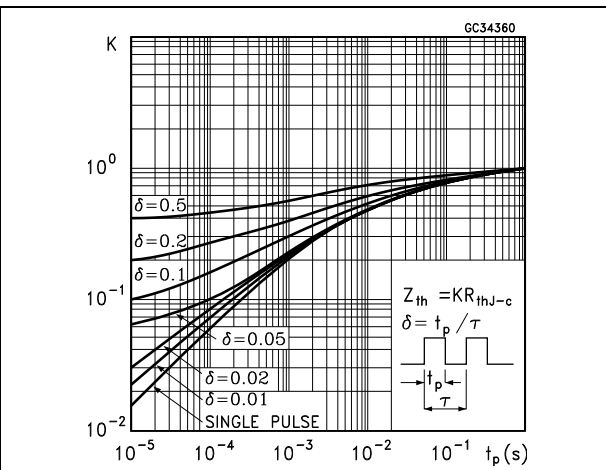


Figure 4. Safe operating area for TO-220FP

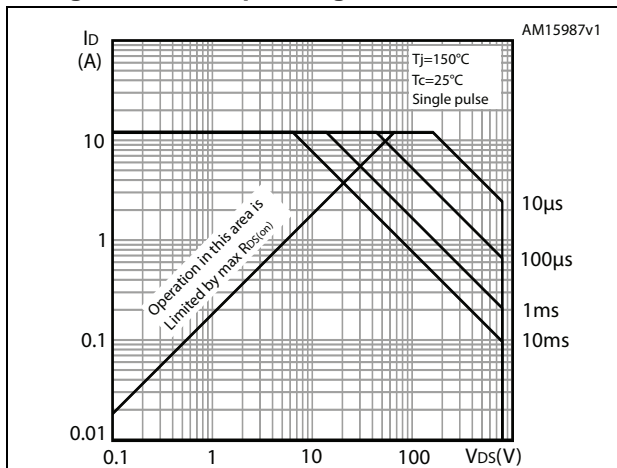


Figure 5. Thermal impedance for TO-220FP

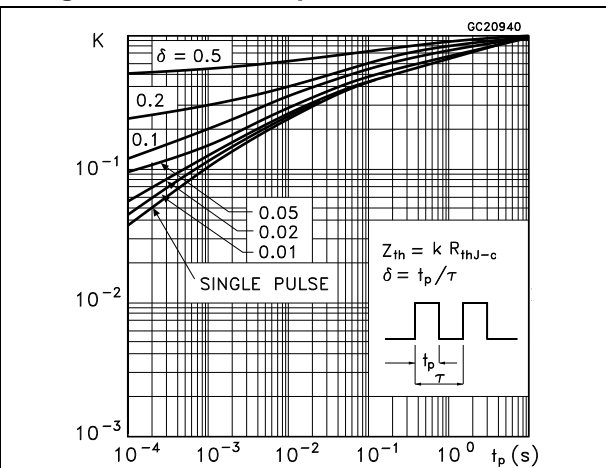


Figure 6. Safe operating area for TO-220

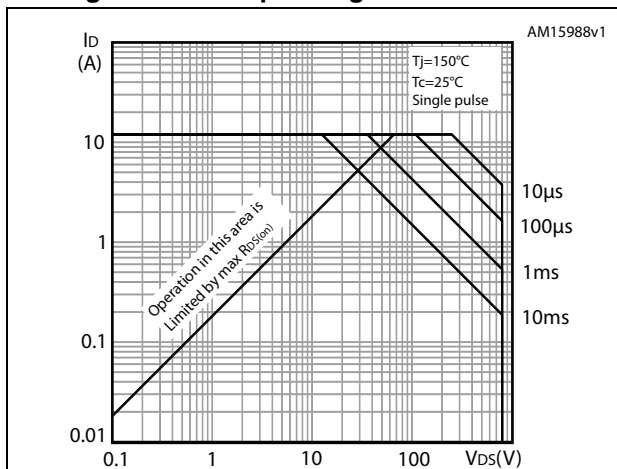


Figure 7. Thermal impedance for TO-220

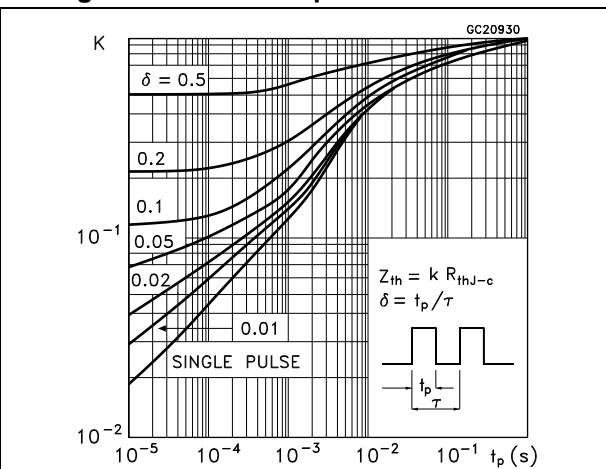


Figure 8. Output characteristics

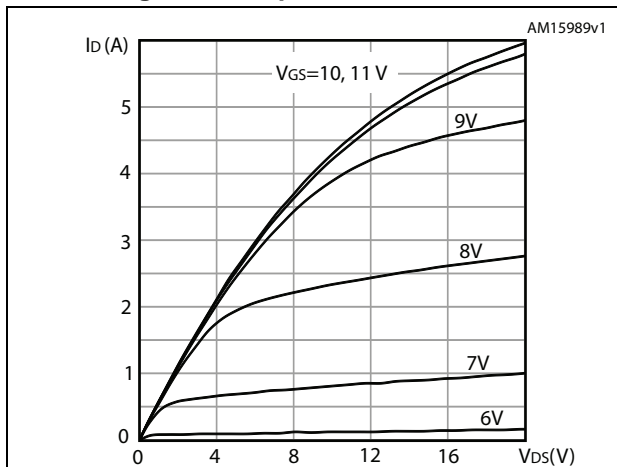


Figure 9. Transfer characteristics

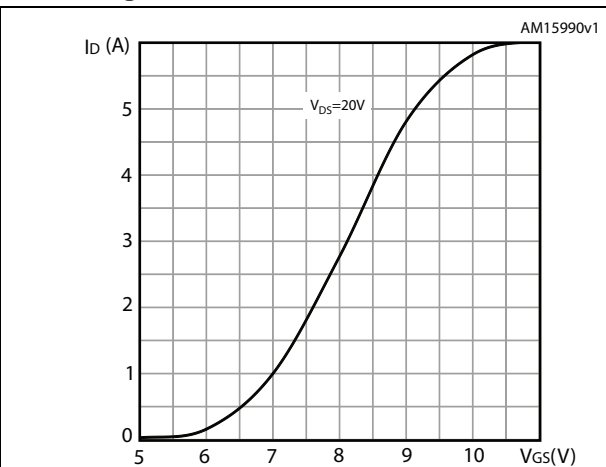


Figure 10. Gate charge vs gate-source voltage

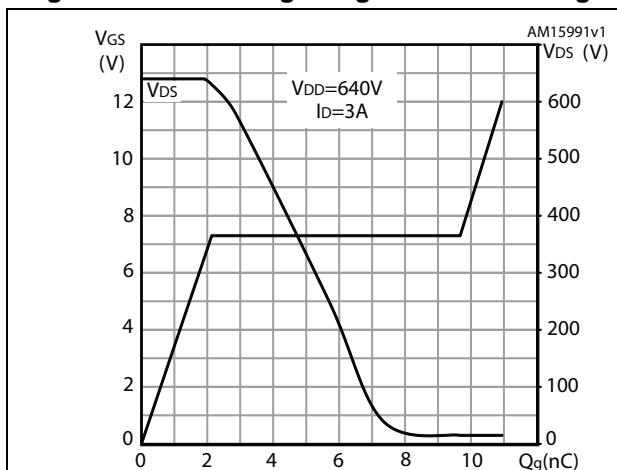


Figure 11. Static drain-source on-resistance

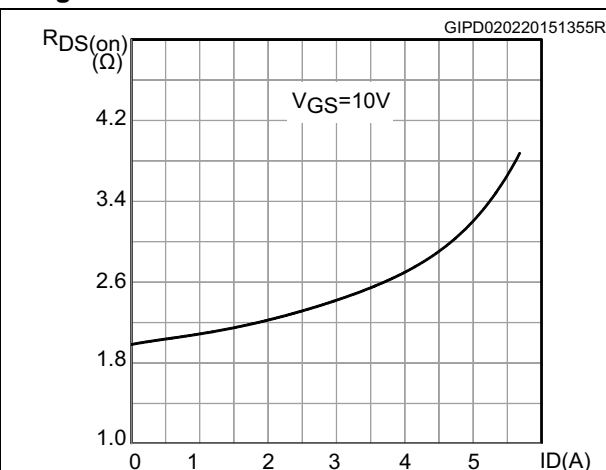


Figure 12. Capacitance variations

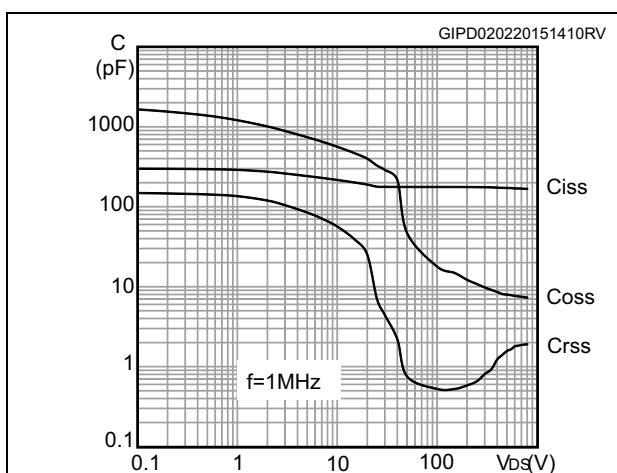


Figure 13. Normalized gate threshold voltage vs temperature

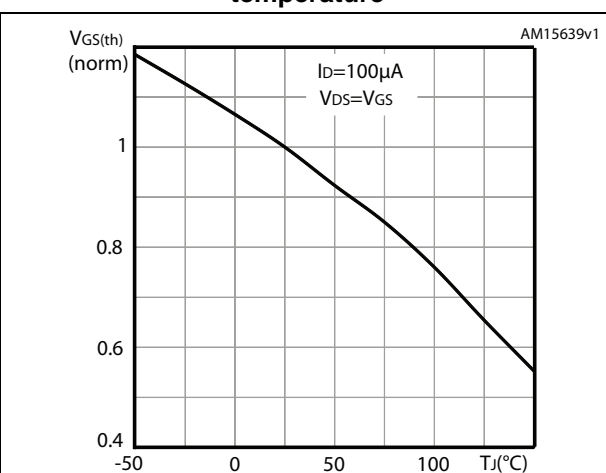


Figure 14. Normalized on-resistance vs temperature

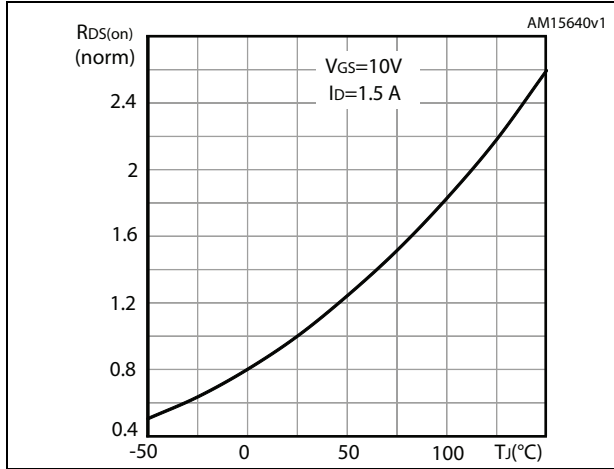


Figure 15. Source-drain diode forward characteristics

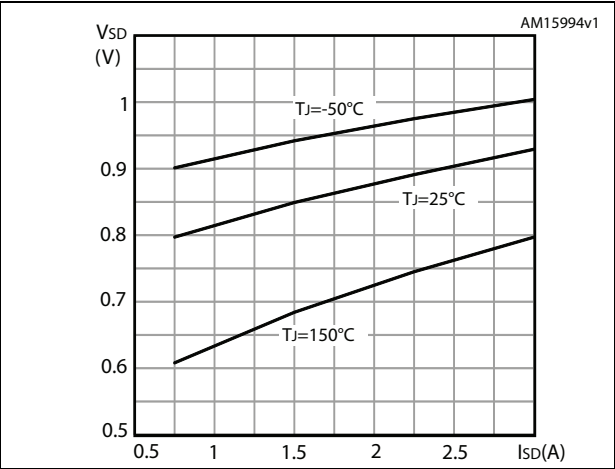


Figure 16. Normalized V<sub>DS</sub> vs temperature

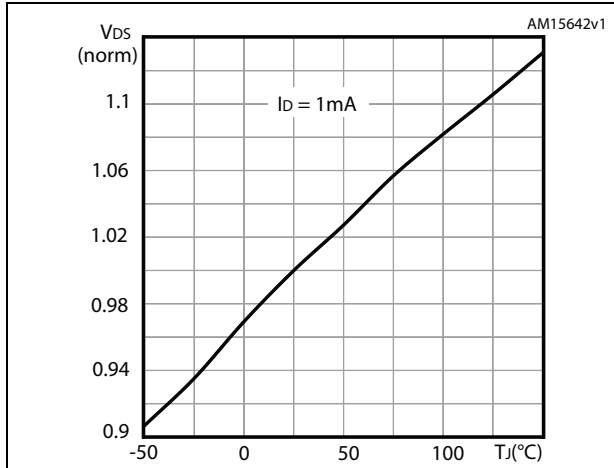
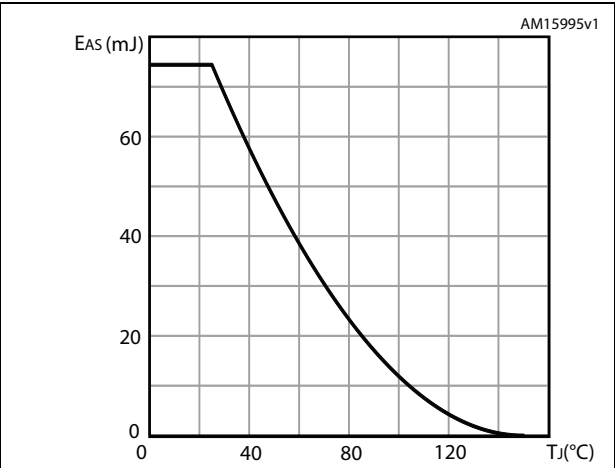


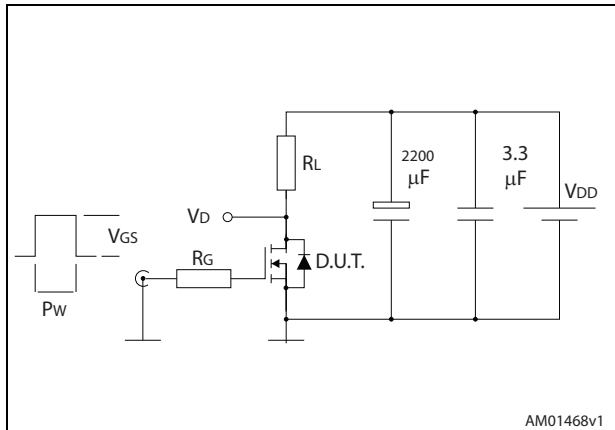
Figure 17. Maximum avalanche energy vs. starting T<sub>J</sub>





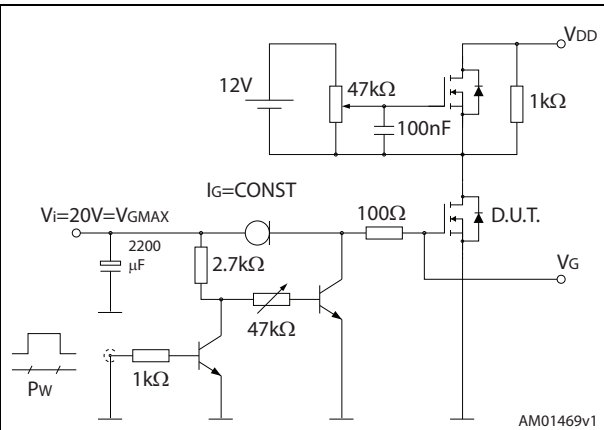
### 3 Test circuits

Figure 18. Switching times test circuit for resistive load



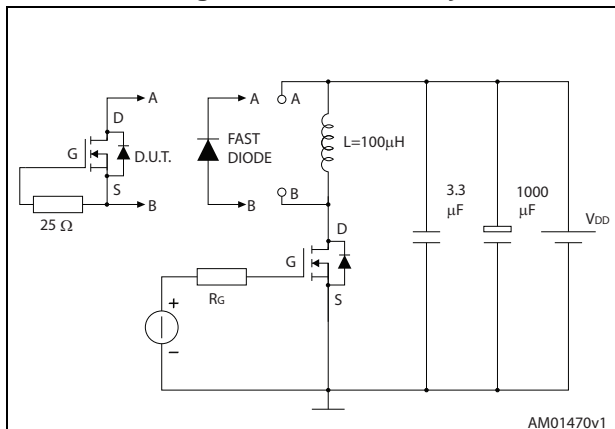
AM01468v1

Figure 19. Gate charge test circuit



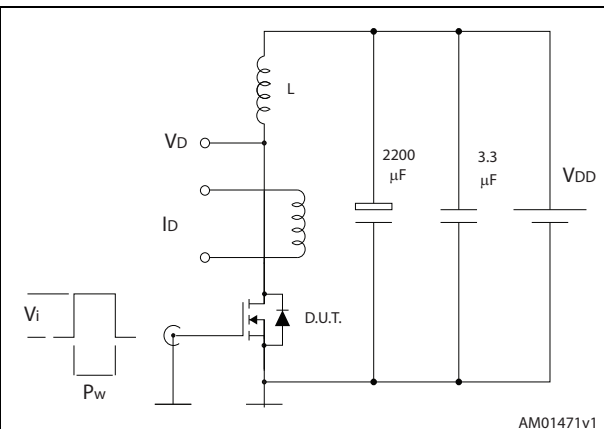
AM01469v1

Figure 20. Test circuit for inductive load switching and diode recovery times



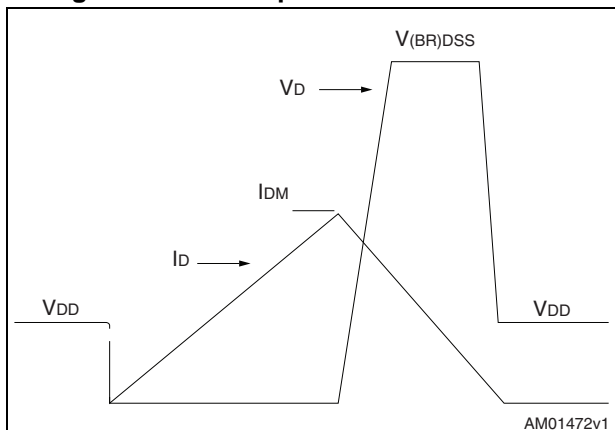
AM01470v1

Figure 21. Unclamped inductive load test circuit



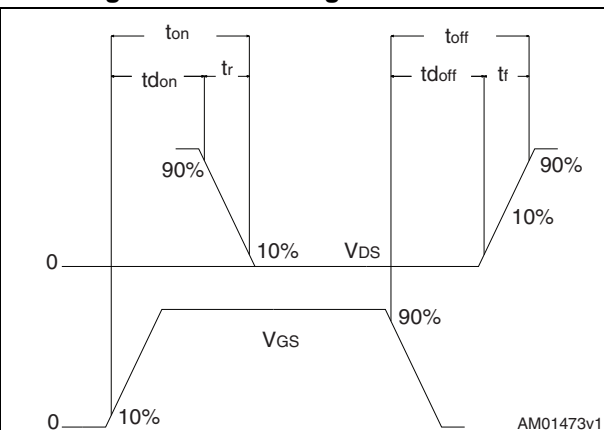
AM01471v1

Figure 22. Unclamped inductive waveform



AM01472v1

Figure 23. Switching time waveform



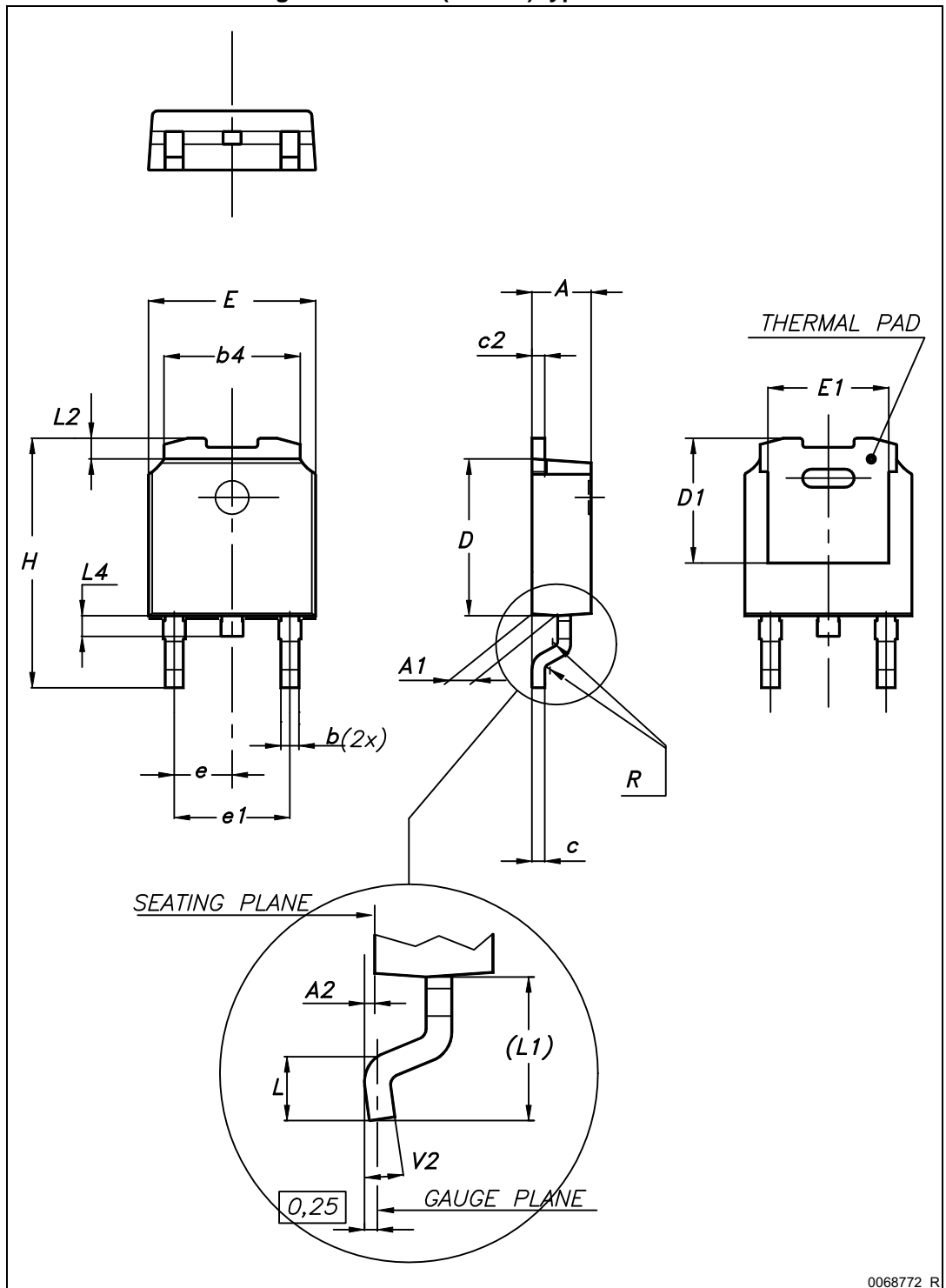
AM01473v1

## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

### 4.1 DPAK(TO-252), package information

Figure 24. DPAK (TO-252) type A outline

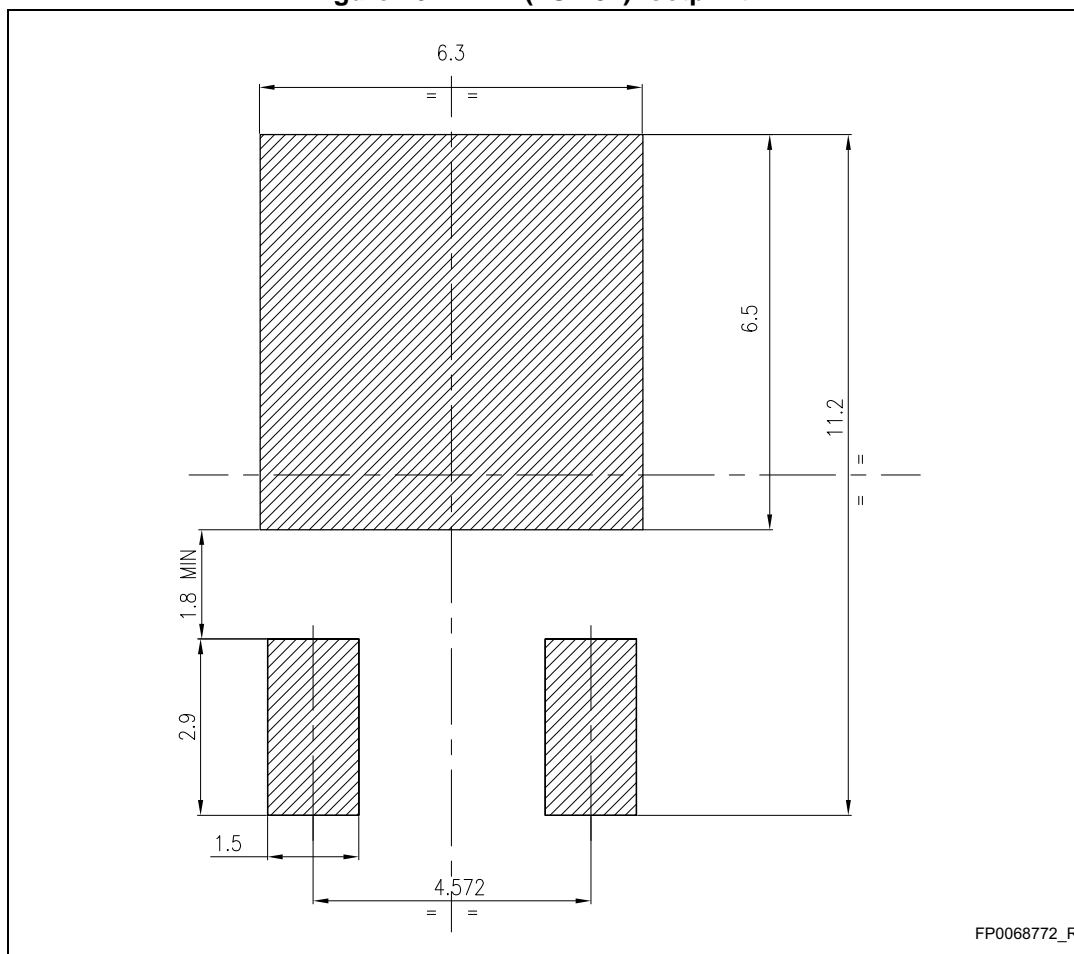


0068772\_R

Figure 25. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

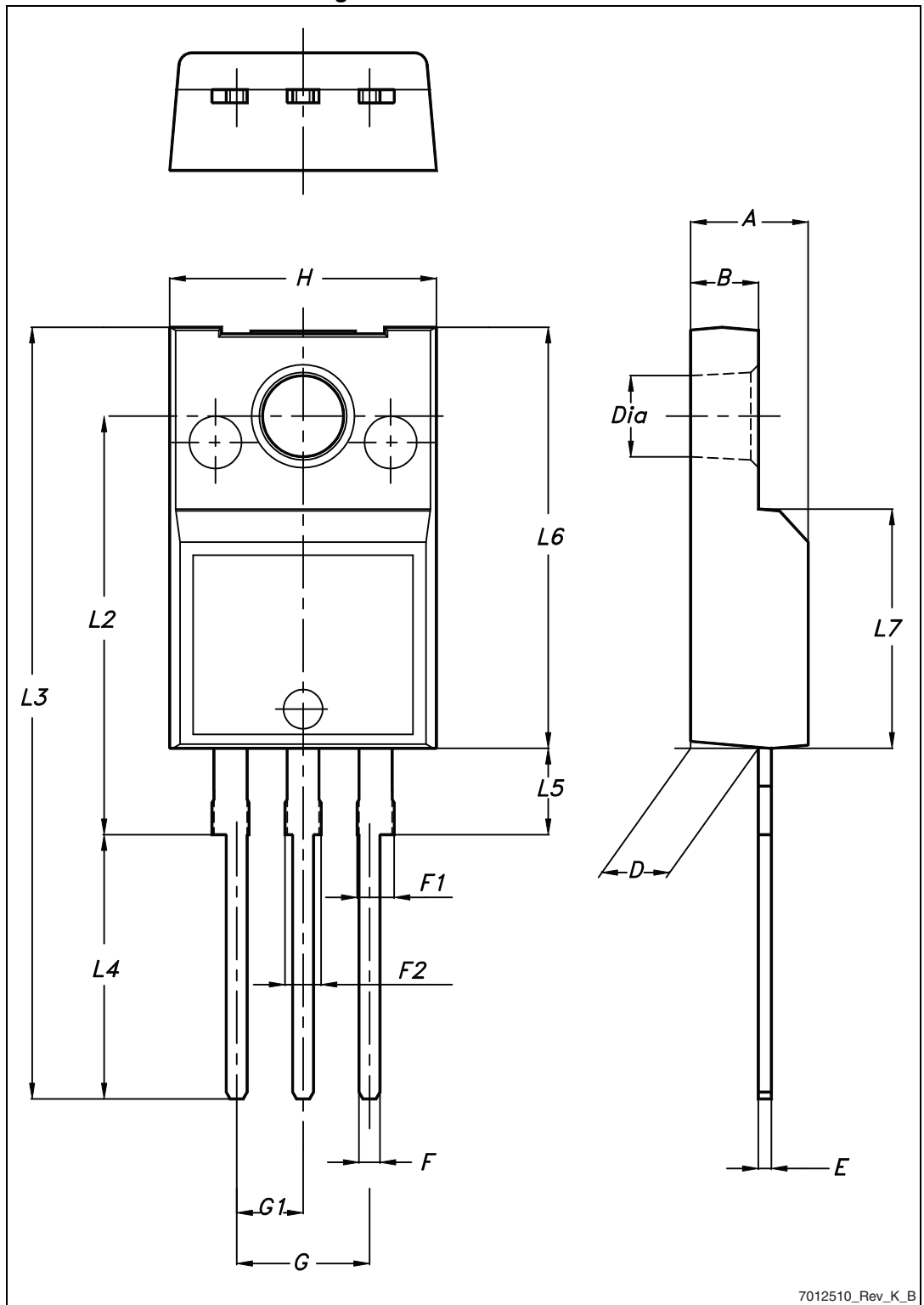
Figure 26. DPAK (TO-252) footprint (a)



a. All dimensions are in millimeters

### 4.2 TO-220FP, package information

Figure 27. TO-220FP outline



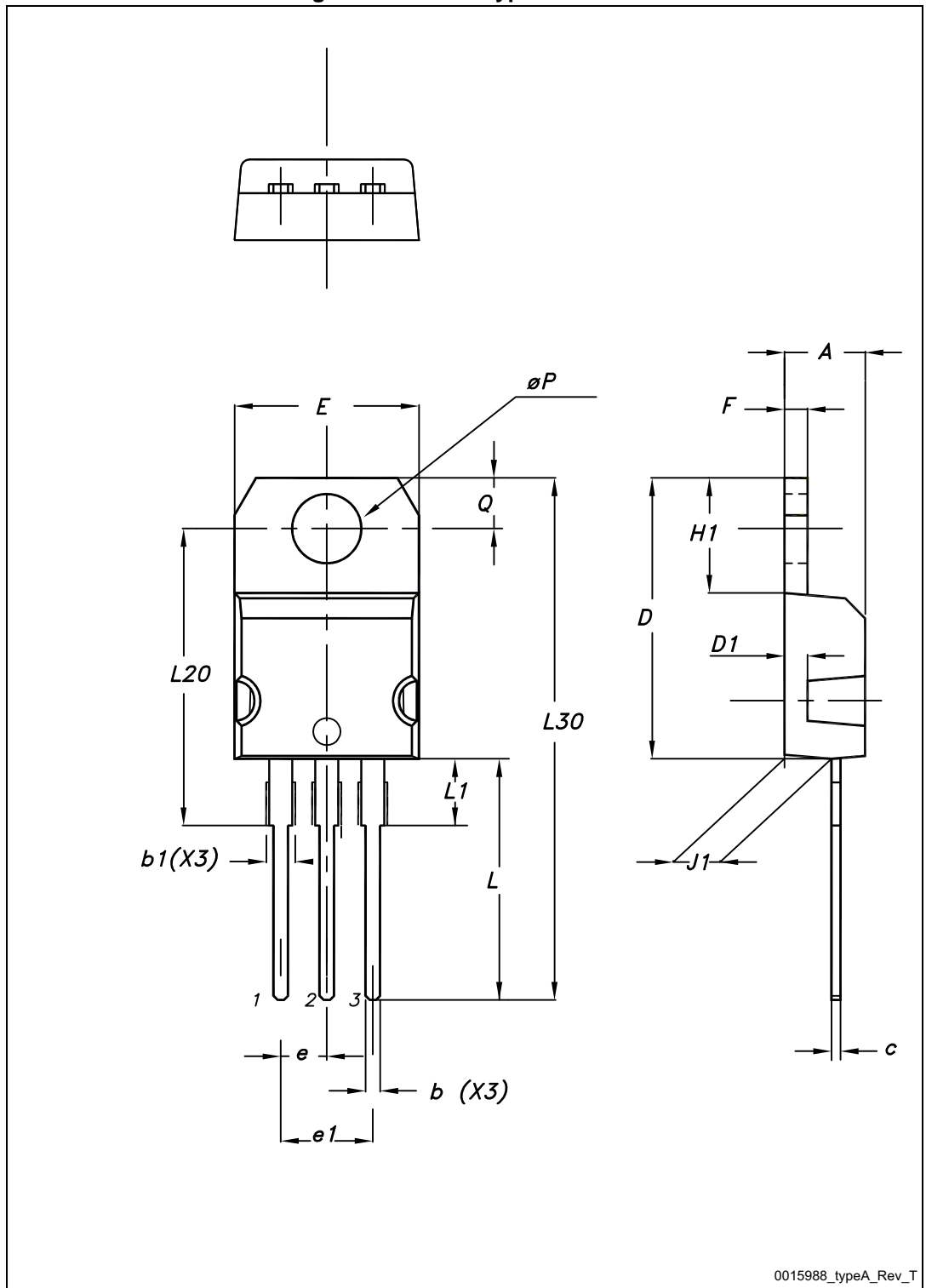
7012510\_Rev\_K\_B

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

### 4.3 TO-220, package information

Figure 28. TO-220 type A outline



0015988\_typeA\_Rev\_T

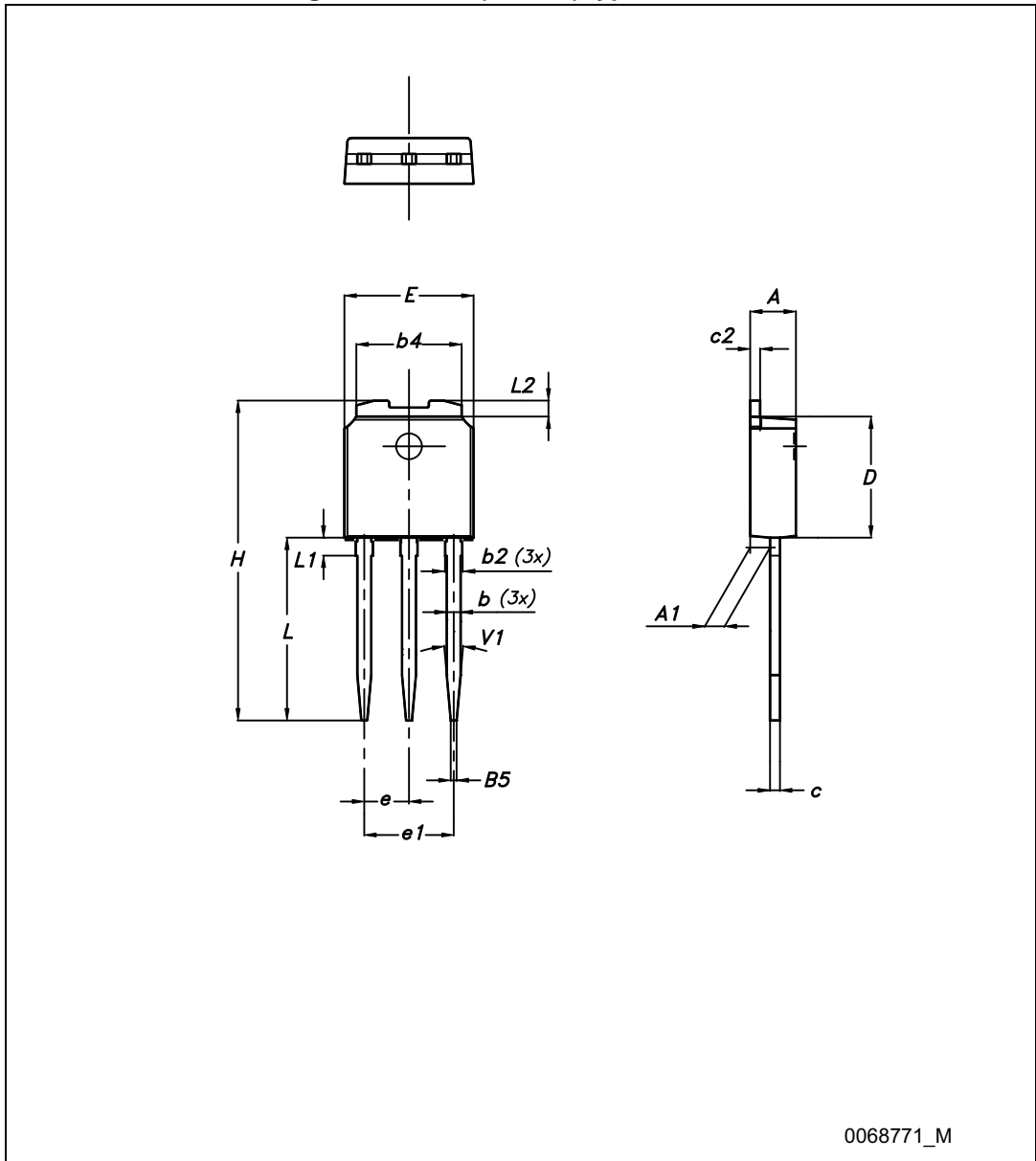


Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

### 4.4 IPAK(TO-251), package information

Figure 29. IPAK (TO-251) type A outline



0068771\_M

Table 11. IPAK (TO-251) type A mechanical data

DIM	mm.		
	min.	typ.	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

## 5 Packaging mechanical data

Table 12. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 30. Tape for DPAK (TO-252)

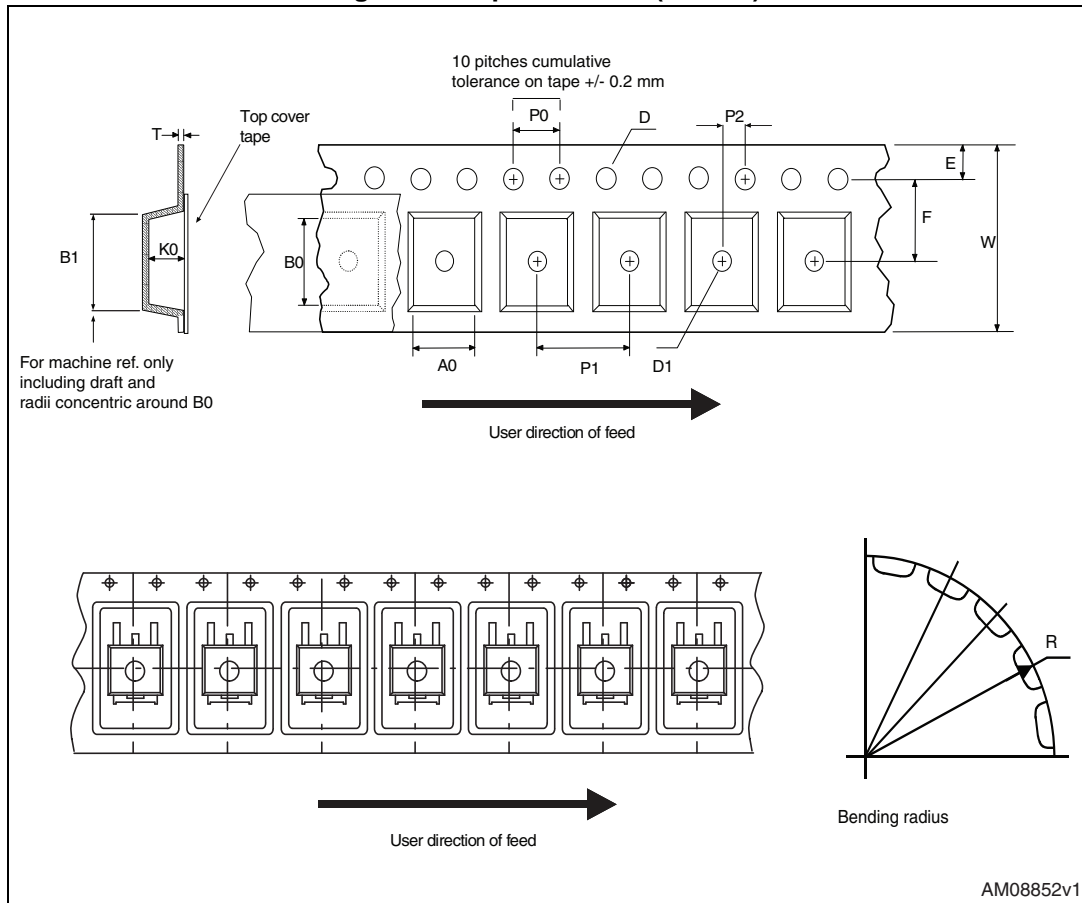
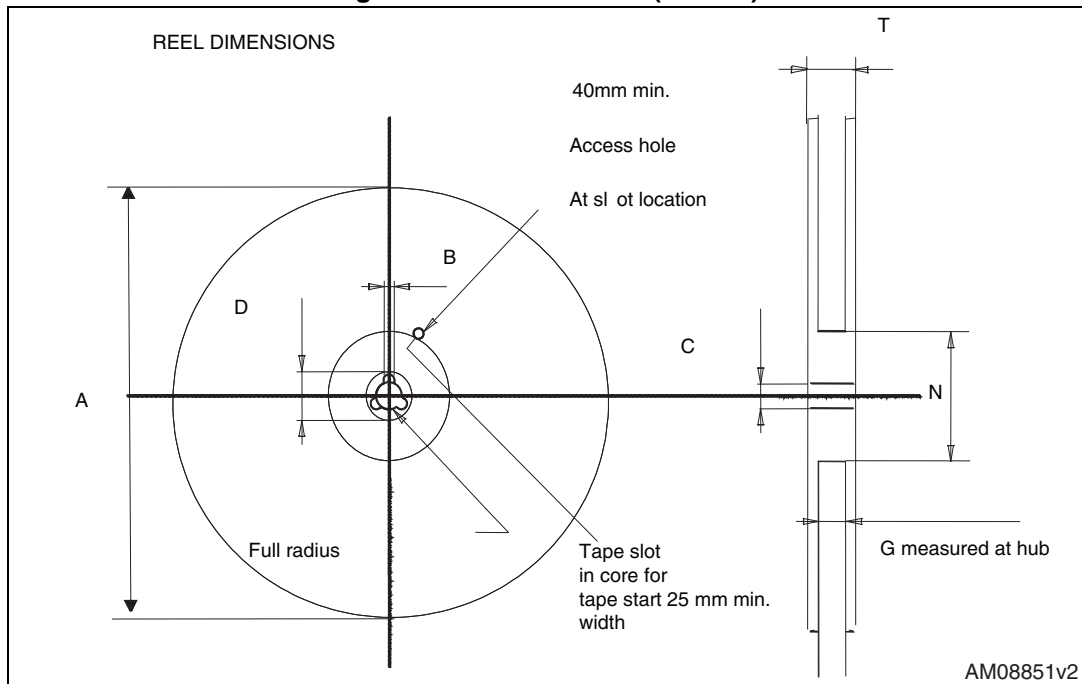


Figure 31. Reel for DPAK (TO-252)



## 6 Revision history

Table 13. Document revision history

Date	Revision	Changes
09-Aug-2013	1	First release
13-Dec-2013	2	<ul style="list-style-type: none"><li>– Added: IPAK package</li><li>– Added: <a href="#">Table 11</a> and <a href="#">Figure 29</a></li><li>– Minor text changes</li></ul>
04-Feb-2015	3	<ul style="list-style-type: none"><li>– Updated title and description in cover page.</li><li>– Updated <a href="#">Table 2.: Absolute maximum ratings</a>, <a href="#">Table 5.: Dynamic</a> and <a href="#">Table 7.: Source drain diode</a>.</li><li>– Updated <a href="#">4: Package information</a> and <a href="#">5: Packaging mechanical data</a>.</li><li>– Minor text changes.</li></ul>

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